

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1214	257/684	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:35
L2	2090	257/734	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:41
L3	2674	257/786	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:02
L4	2051	257/713	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:04
L5	103	257/909	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:08
L6	1581	438/113	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:09
L7	581	438/114	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:20
L8	936	438/435	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:20

EAST Search History

S1	4318	(interposer or interconnect\$3 or redistribution) and dam	USPAT	OR	ON	2006/04/26 12:56
S2	3077	(semiconductor or die or chip or IC) and (interposer or interconnect\$3 or redistribution) and dam	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 13:55
S3	1676	(semiconductor or die or chip or IC) and (interposer or interconnect\$3 or redistribution) and dam	USPAT; JPO	OR	ON	2004/12/06 17:06
S4	3	(semiconductor or die or chip or IC) and (interposer or interconnect\$3 or redistribution) and dam	EPO	OR	ON	2004/12/06 17:06
S5	7	"6333564"	USPAT	OR	OFF	2004/12/06 17:09
S6	1	"9639319"	USOCR; DERWENT; IBM_TDB	OR	OFF	2004/12/06 17:25
S7	0	"96039319"	USOCR; DERWENT; IBM_TDB	OR	OFF	2004/12/06 17:17
S8	0	"09639319"	USOCR; DERWENT; IBM_TDB	OR	OFF	2004/12/06 17:17
S9	1	"6013946"	USOCR; DERWENT; IBM_TDB	OR	OFF	2004/12/06 17:26
S10	46	"6013946"	USPAT	OR	OFF	2004/12/06 17:28
S11	1	"6013946"	USOCR; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/06 17:27
S12	1	"10098130"	JPO	OR	OFF	2004/12/06 17:27
S13	1	"6013946".pn. and dam with (polymer or material)	USPAT	OR	ON	2004/12/06 17:32
S14	1	"6013946".pn. and dam with (insulat\$ or formed)	USPAT	OR	ON	2004/12/06 17:45
S15	1	"6630730".pn.	USPAT	OR	ON	2004/12/06 17:48
S16	0	(semiconductor or die or chip or IC) and adhesive with photopolymer and dam with photopolymer	USPAT	OR	ON	2004/12/06 17:50
S17	4	(semiconductor or die or chip or IC) and dam with photopolymer	USPAT	OR	ON	2004/12/06 17:50

EAST Search History

S18	74	(semiconductor or die or chip or IC) and photopolymer with epoxy	USPAT	OR	ON	2004/12/06 18:06
S19	0	(semiconductor or die or chip or IC) and photopolymer with epoxy and dam with epoxy	USPAT	OR	ON	2004/12/06 17:51
S20	0	(semiconductor or die or chip or IC) and photopolymer with epoxy and dam same epoxy	USPAT	OR	ON	2004/12/06 17:52
S21	244	(semiconductor or die or chip or IC) and dam with epoxy	USPAT	OR	ON	2004/12/06 17:52
S22	25	(semiconductor or die or chip or IC) and dam near epoxy	USPAT	OR	ON	2004/12/06 17:52
S23	13	(semiconductor or die or chip or IC) and dam near epoxy and adhesive with epoxy	USPAT	OR	ON	2004/12/06 17:52
S24	4	(semiconductor or die or chip or IC) and photopolymer with epoxy and dam	USPAT	OR	ON	2004/12/06 17:59
S25	1	(semiconductor or die or chip or IC) and photopolymer with epoxy and adhesive with between with (semiconductor or die or chip or IC)	USPAT	OR	ON	2004/12/06 18:00
S26	7	(semiconductor or die or chip or IC) and photopolymer with epoxy and adhesive with (semiconductor or die or chip or IC)	USPAT	OR	ON	2004/12/06 18:01
S27	10	(semiconductor or die or chip or IC) and photopolymer with (epoxy or polyimide) and adhesive with (semiconductor or die or chip or IC)	USPAT	OR	ON	2004/12/06 18:03
S28	1	(semiconductor or die or chip or IC) and photopolymer near material with epoxy	USPAT	OR	ON	2004/12/06 18:08
S29	244	(semiconductor or die or chip or IC) and dam with epoxy	USPAT	OR	ON	2004/12/06 18:08
S30	5	(semiconductor or die or chip or IC) and dam with epoxy and (adheave or glue) with epoxy	USPAT	OR	ON	2004/12/06 18:09
S31	5	(semiconductor or die or chip or IC) and dam with epoxy and (adheave or glue or attaching near material) with epoxy	USPAT	OR	ON	2004/12/06 18:10
S32	244	(semiconductor or die or chip or IC) and dam with epoxy	USPAT	OR	ON	2004/12/06 18:10

EAST Search History

S33	95	(semiconductor or die or chip or IC) and dam with epoxy and dam with (layers or films)	USPAT	OR	ON	2004/12/06 18:11
S34	32	(semiconductor or die or chip or IC) and dam with epoxy and dam with formed with(layers or films)	USPAT	OR	ON	2004/12/07 12:55
S35	3	((("d415420") or ("6056138") or ("6196404")).PN.	USPAT	OR	OFF	2004/12/07 12:56
S36	0	("(semiconductorordieorchiporIC)anddamwith(photopolymerorepoxy)").PN.	USPAT	OR	OFF	2004/12/07 18:42
S37	233	(semiconductor or die or chip or IC) and dam with (photopolymer or epoxy)	USPAT	OR	OFF	2004/12/07 18:43
S38	4	(semiconductor or die or chip or IC) and dam with (photopolymer)	USPAT	OR	OFF	2004/12/07 18:43
S39	89	(semiconductor or die or chip or IC) and dam with (epoxy) and adhesive with epoxy	USPAT	OR	OFF	2004/12/07 20:26
S40	9	(semiconductor or die or chip or IC) and dam near epoxy and adhesive near epoxy	USPAT	OR	OFF	2004/12/07 19:00
S41	1097	(semiconductor or die or chip or IC) and heat near (sink or dissipat\$3 or spread\$3 or transfer) with ground	USPAT	OR	OFF	2004/12/07 19:26
S42	262	S41 and ground with via	USPAT	OR	OFF	2004/12/07 19:26
S43	89	S39 and (semiconductor or die or chip or IC) and dam and (epoxy) and adhesive with epoxy	USPAT	OR	OFF	2004/12/07 20:26
S44	89	S39 and (semiconductor or die or chip or IC) and dam and (epoxy) and adhesive with epoxy	USPAT	OR	ON	2004/12/07 21:50
S45	2258	257/734	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 22:06
S46	5520	257/666	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 22:18

EAST Search History

S47	995	257/667	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 22:29
S48	2764	257/786	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 22:38
S49	4	"5734201".pn. or "6529027".pn. or "199716954".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 22:37
S50	2204	257/713	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 22:54
S51	417	257/909	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 23:09
S52	25	"6251488".pn. or "6259962".pn. or "6268584".pn. or "6391251". pn. or "6468891".pn. or "6500746".pn. or "6524346".pn. or "6537842".pn. or "6544902". pn. or "6611053".pn. or "6632732".pn. or "6634100".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 22:58
S53	12	"6251488".pn. or "6259962".pn. or "6268584".pn. or "6391251". pn. or "6468891".pn. or "6500746".pn. or "6524346".pn. or "6537842".pn. or "6544902". pn. or "6611053".pn. or "6632732".pn. or "6634100".pn.	USPAT	OR	ON	2004/12/07 23:05

EAST Search History

S54	11	"20020102829".pn. or "20020111003".pn. or "20020171177".pn. or "20030045047".pn. or "20030098470".pn. or "20030102566".pn. or "20030141885".pn. or "20030151167".pn. or "20030180974".pn. or "20030181003".pn. or "20030186496".pn.	US-PGPUB; USPAT	OR	ON	2004/12/07 23:08
S55	1432	438/113	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 23:13
S56	467	438/114	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 23:25
S57	23	"4143456".pn. or "4218701".pn. or "4843036".pn. or "5173220". pn. or "5259793".pn. or "5264061".pn. or "5278442".pn. or "5336931".pn. or "5484314". pn. or "5574310".pn. or "5705117".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 23:23
S58	11	"4143456".pn. or "4218701".pn. or "4843036".pn. or "5173220". pn. or "5259793".pn. or "5264061".pn. or "5278442".pn. or "5336931".pn. or "5484314". pn. or "5574310".pn. or "5705117".pn.	USPAT	OR	ON	2004/12/07 23:24
S59	11	"5,714,800".pn. or "5,714,802". pn. or "5,719,440".pn. or "5,767, 443".pn. or "5,793,116".pn. or "5, 834,830".pn. or "5,866,949".pn. or "5,920,118".pn. or "5,965,933". pn. or "5,977,640".pn. or "5,994, 166".pn.	USPAT	OR	ON	2004/12/07 23:39
S60	770	438/435	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 23:25

EAST Search History

S61	12	"5,999,413".pn. or "6,013,946".pn. or "6,091,140".pn. or "6,124,407".pn. or "6,222,263".pn. or "6,239,013".pn. or "6,300,165".pn. or "6,372,552".pn. or "6,380,557".pn. or "6,448,664".pn. or "6,489,183".pn. or "6,522,019".pn.	USPAT	OR	ON	2004/12/07 23:40
S62	271	(semiconductor or chip or die or dice or IC) and (interposer or interconnect\$3 or redistribution) and dam with (layers or films)	USPAT	OR	ON	2005/05/17 15:57
S63	34	(semiconductor or chip or die or dice or IC) and (interposer or interconnect\$3 or redistribution) and dam near (layers or films)	USPAT	OR	ON	2005/05/17 15:45
S64	6	(semiconductor or chip or die or dice or IC) and (interposer or interconnect\$3 or redistribution) and dam near (layers or films) same dam with metal\$3	USPAT	OR	ON	2005/05/17 15:34
S65	8	(semiconductor or chip or die or dice or IC) and (interposer or interconnect\$3 or redistribution) and dam near (layers or films) same dam with (metal\$3 or copper or "Cu")	USPAT	OR	ON	2005/05/17 15:36
S66	61	(semiconductor or chip or die or dice or IC) and dam near (layers or films)	USPAT	OR	ON	2005/05/17 15:57
S67	27	S66 not S63	USPAT	OR	ON	2005/05/17 15:46
S68	655	(semiconductor or chip or die or dice or IC) and dam with (layers or films)	USPAT	OR	ON	2005/05/17 16:53
S69	271	S62 not S67	USPAT	OR	ON	2005/05/17 15:58
S70	237	S62 not S66	USPAT	OR	ON	2005/05/17 15:58
S71	22	(semiconductor or chip or die or dice or IC) and dam near multi\$5	USPAT	OR	ON	2005/05/17 16:33
S72	16	(semiconductor or chip or die or dice or IC) and dam with multi\$5 near (layers or films)	USPAT	OR	ON	2005/05/17 16:33
S73	2	(semiconductor or chip or die or dice or IC) and multi\$5 near (layers or films) near dam	USPAT	OR	ON	2005/05/17 16:53
S74	2	(semiconductor or chip or die or dice or IC) and multi\$5 near (layer or film) near dam	USPAT	OR	ON	2005/05/17 16:53

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S75	2	(semiconductor or chip or die or dice or IC) and multi\$5 near (layer or film) near dam	USPAT; JPO	OR	ON	2005/05/17 16:56
S76	1	(semiconductor or chip or die or dice or IC) and two near (layer or film) near dam	USPAT; JPO	OR	ON	2005/05/17 16:57
S77	6	(semiconductor or chip or die or dice or IC) and two with (layer or film) near dam	USPAT; JPO	OR	ON	2005/05/17 16:58
S78	2	(semiconductor or chip or die or dice or IC) and multi\$5 with (layer or film) near dam	USPAT; JPO	OR	ON	2005/05/17 17:31
S79	1	"6479887".pn. and dam with (around or surround\$3)	USPAT	OR	ON	2005/05/17 17:26
S80	1	(semiconductor or chip or die or dice or IC) and laminat\$3 with (layer or film) near dam	USPAT; JPO	OR	ON	2005/05/17 17:32
S81	1	(semiconductor or chip or die or dice or IC) and (laminat\$3 or dual or double) with (layer or film) near dam	USPAT; JPO	OR	ON	2005/05/17 17:32
S82	44	(semiconductor or chip or die or dice or IC) and (laminat\$3 or dual or double) with (layer or film) with dam	USPAT; JPO	OR	ON	2005/05/17 17:38
S83	16	(semiconductor or chip or die or dice or IC) and (dual or double) with (layer or film) with dam	USPAT; JPO	OR	ON	2005/05/17 17:38
S84	6	(semiconductor or chip or die or dice or IC) and (dual or double) near (layer or film) with dam	USPAT; JPO	OR	ON	2005/05/17 17:38
S85	1	("3627338".pn. or "4906011".pn.) and porous	USPAT	OR	OFF	2005/05/19 16:11
S86	0	("3627338".pn. or "4906011".pn.) and porous near plate	USPAT	OR	OFF	2005/05/19 15:34
S87	29	"6322903"	USPAT	OR	OFF	2005/05/19 17:49
S88	1769	257/734	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/19 17:51

EAST Search History

S89	3865	257/666	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/19 17:51
S90	0	"6479887".pn. and adhesive with epoxy	USPAT	OR	OFF	2005/05/26 20:31
S91	0	"6479887".pn. and solder near resist with prevent\$3 with overflow	USPAT	OR	ON	2005/08/19 13:21
S92	1	"6479887".pn. and solder near mask with prevent\$3 with overflow	USPAT	OR	ON	2005/08/19 13:23
S93	1	"6479887".pn. and solder near mask and prevent\$3 with overflow	USPAT	OR	ON	2005/08/19 13:23
S94	40	"6091140"	USPAT	OR	OFF	2005/11/03 18:05
S95	0	"6091140" and wall with multi\$4	USPAT	OR	ON	2005/11/03 16:19
S96	6325	(semiconductor or die or dice or chip or IC) and (wall or dam) with multi\$4	USPAT	OR	ON	2005/11/03 16:20
S97	146	(semiconductor or die or dice or chip or IC) and (dam) with multi\$4	USPAT	OR	ON	2005/11/03 16:36
S98	13	(semiconductor or die or dice or chip or IC) and (dam) with (multi near layers or multi-layers)	USPAT	OR	ON	2005/11/03 16:39
S99	557	(semiconductor or die or dice or chip or IC) and (wall) with (multi near layers or multi-layers)	USPAT	OR	ON	2005/11/03 16:39
S10 0	0	(semiconductor or die or dice or chip or IC) and (dam) with (multi near films or multi-films)	USPAT	OR	ON	2005/11/03 16:39
S10 1	125	(semiconductor or die or dice or chip or IC) and (wall) with (multi near layers or multi-layers) and wall with (mold\$3 or encapsulat\$3)	USPAT	OR	ON	2005/11/03 16:41
S10 2	75	(semiconductor or die or dice or chip or IC) and (wall) with (multi near layers or multi-layers) and wall with (mold\$3 or encapsulat\$3) and wall with (window or open\$3 or hole)	USPAT	OR	ON	2005/11/03 16:51
S10 3	3	(semiconductor or die or dice or chip or IC) and (dam) with (multi near layers or multi-layers)	US-PGPUB; JPO	OR	ON	2005/11/03 16:52

EAST Search History

S10 4	1	(semiconductor or die or dice or chip or IC) and (dam) and (multi near layers or multi-layers)	JPO	OR	ON	2005/11/03 17:00
S10 5	0	(semiconductor or die or dice or chip or IC) and (dam) with (multiful near layers or multiful-layers)	JPO	OR	ON	2005/11/03 17:00
S10 6	0	(semiconductor or die or dice or chip or IC) and (dam) with (multi near layers or multiful-layers)	JPO	OR	ON	2005/11/03 17:00
S10 7	0	(semiconductor or die or dice or chip or IC) and (dam) with (multi near layers or multi-layers)	JPO	OR	ON	2005/11/03 17:00
S10 8	0	(semiconductor or die or dice or chip or IC) and (dam) with (multiful near layers or multiful-layers)	USPAT	OR	ON	2005/11/03 17:00
S10 9	521	(semiconductor or die or dice or chip or IC) and (dam) with (layers or multiful-layers)	USPAT	OR	ON	2005/11/03 17:01
S11 0	676	(semiconductor or die or dice or chip or IC) and (dam) with (layers or films)	USPAT	OR	ON	2005/11/03 17:01
S11 1	63	(semiconductor or die or dice or chip or IC) and (dam) near (layers or films)	USPAT	OR	ON	2005/11/03 17:10
S11 2	1	(semiconductor or die or dice or chip or IC) and (dam) near (two-layers or two near (layers or films))	USPAT	OR	ON	2005/11/03 17:11
S11 3	11	(semiconductor or die or dice or chip or IC) and (dam) with (two-layers or two near (layers or films))	USPAT	OR	ON	2005/11/03 17:13
S11 4	25	(semiconductor or die or dice or chip or IC) and (dam) with (top-layers or (top or upper or bottom or lower) near (layers or films))	USPAT	OR	ON	2005/11/03 17:17
S11 5	2131	(semiconductor or die or dice or chip or IC) and (wall) with (top-layers or (top or upper or bottom or lower) near (layers or films))	USPAT	OR	ON	2005/11/03 17:18

EAST Search History

S11 6	1073	(semiconductor or die or dice or chip or IC) and (wall) with (top-layers or (top or upper or bottom or lower) near (layers or films)) and wall with (window or open\$3 or hole)	USPAT	OR	ON	2005/11/03 17:18
S11 7	93	(semiconductor or die or dice or chip or IC) and (wall) with (top-layers or (top or upper or bottom or lower) near (layers or films)) and wall with (window or open\$3 or hole) and wall with (mold\$3 or encapsulat\$3)	USPAT	OR	ON	2005/11/03 17:26
S11 8	140	(semiconductor or die or dice or chip or IC) and (wall) with (multi-layers or (top or upper or bottom or lower) near (layers or films)) and wall with (window or open\$3 or hole) and wall with (mold\$3 or encapsulat\$3)	USPAT	OR	ON	2005/11/03 17:26
S11 9	163	(semiconductor or die or dice or chip or IC) and (wall) with (multi-layers or (top or upper or bottom or lower or multi\$4) near (layers or films)) and wall with (window or open\$3 or hole) and wall with (mold\$3 or encapsulat\$3)	USPAT	OR	ON	2005/11/07 12:52
S12 0	70	S119 not S117	USPAT	OR	ON	2005/11/03 17:27
S12 1	117	"5436203"	USPAT	OR	OFF	2005/11/03 18:05
S12 2	2	(semiconductor or die or dice or chip or IC) and (dam) with (multi-layers or (top or upper or bottom or lower or multi\$4) near (layers or films)) and wall with (window or open\$3 or hole) and wall with (mold\$3 or encapsulat\$3)	USPAT	OR	ON	2005/11/07 12:53
S12 3	40	(semiconductor or die or dice or chip or IC) and (dam) with (multi-layers or (top or upper or bottom or lower or multi\$4) near (layers or films))	USPAT	OR	ON	2005/11/07 15:26
S12 4	18	"5744084"	USPAT	OR	ON	2005/11/07 13:26
S12 5	121	(semiconductor or die or dice or chip or IC) and (dam) with (projection or protru\$4)	USPAT	OR	ON	2005/11/07 17:34

EAST Search History

S12 6	1132	257/684	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/07 16:45
S12 7	1932	257/734	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/07 17:44
S12 8	0	(semiconductor or die or dice or chip or IC) and (dam) with (photopolymer) same ("FR4" or "BT" near resin or teflon)	USPAT	OR	ON	2005/11/07 17:35
S12 9	2	(semiconductor or die or dice or chip or IC) and (photopolymer) with ("FR4" or "BT" near resin or teflon)	USPAT	OR	ON	2005/11/07 17:35
S13 0	4109	257/666	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/07 17:54
S13 1	828	257/667	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/07 17:54
S13 2	4371	257/666	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 12:58
S13 3	866	257/667	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:31
S13 4	3	257/e23.055	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 13:07